



2:1 MIPI 2-Data Lane Switch

### **Description**

The DIODES PI3WVR626 is a two-data-lane MIPI switch. This 6 channel single-pole, double-throw (SPDT) switch is optimized for switching between two high-speed (HS) or low-power (LP) MIPI signal. The PI3WVR626 is designed for the MIPI specification and allows connection to CSI/DSI, C-PHY/D-PHY module.

### Application(s)

- Cellular Phones, Smart Phones
- **Tablets**
- Laptops
- Displays

#### **Features**

- 3-lane, 2:1 Switches that support D-PHY and C-PHY
- Data Rate Support: up to 3.5Gsps C-PHY, up to 4.5Gb/s D-PHY.
- Bandwidth: 6GHz Typical
- Low Crosstalk: -35 dB@1.25 GHz
- Input Signals 0 to 1.3V
- R<sub>ON</sub>: 5.0Ω Typical LP & HS MIPI
- $\Delta R_{ON}$ : 0.2 $\Omega$  Typical LP & HS MIPI
- $R_{ON\_FLAT}$ : 0.1 $\Omega$  Typical LP & HS MIPI
- I<sub>CC</sub>: 11µA Typical
- Skew of Opposite Transitions of the Same Output: 5ps Typical
- V<sub>DD</sub> Operating Range: 1.5V to 3.6V
- ESD Tolerance: 2kV HBM
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/104/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/
- Packaging (Pb-free & Green):
  - 24-Pin, X1QFN (2.5mm x 2.5mm) (XEB)

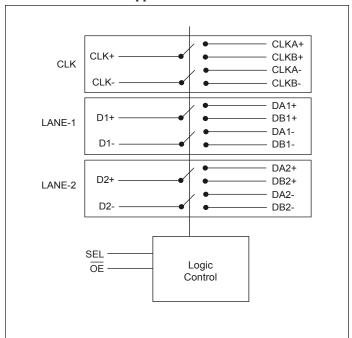
- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.



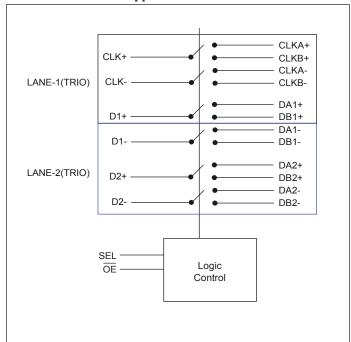


### **Block Diagram**

## PI3WVR626 D-PHY Application



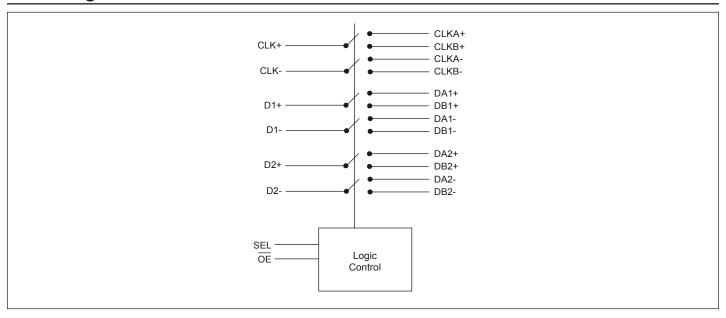
#### PI3WVR626 C-PHY Application







## **Block Diagram**



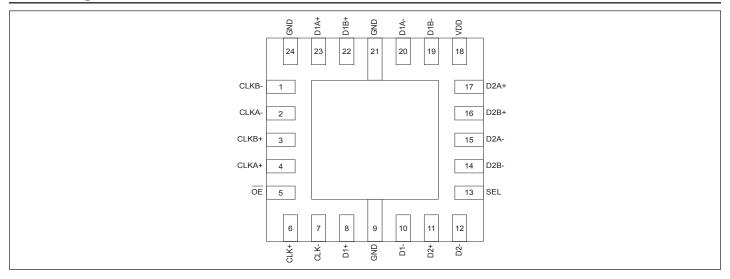
### **Truth Table**

SEL	ŌĒ	Function
LOW	LOW	CLK+ = CLKA+, CLK- = CLKA-, Dn(+/-) = DAn(+/-)
HIGH	LOW	CLK+ = CLKB+, CLK- = CLKB-, Dn(+/-) = DBn(+/-)
X	HIGH	Clock and Data Ports High Impedance





## **Pin Configuration**



## **Pin Description**

Pin#	Pin Name	Type	Description
18	$V_{\mathrm{DD}}$	Power	1.5V to 3.3V power supply
9, 21, 24	GND	Ground	Ground
5	ŌE	I	Output enable. if OE is low, IC is enabled. if OE is high, IC is power down and all I/Os are Hi-Z
13	SEL	I	Switch logic control
14	D2B-	I/O	Negative differential signal 2 for port B
16	D2B+	I/O	Positive differential signal 2 for port B
15	D2A-	I/O	Negative differential signal 2 for port A
17	D2A+	I/O	Positive differential signal 2 for port A
12	D2-	I/O	Negative differential signal 2 for COM port
11	D2+	I/O	Positive differential signal 2 for COM port
19	D1B-	I/O	Negative differential signal 1 for port B
22	D1B+	I/O	Positive differential signal 1 for port B
20	D1A-	I/O	Negative differential signal 1 for port A
23	D1A+	I/O	Positive differential signal 1 for port A
10	D1-	I/O	Negative differential signal 1 for COM port
8	D1+	I/O	Positive differential signal 1 for COM port
1	CLKB-	I/O	Clock negative differential signal for port B
3	CLKB+	I/O	Clock positive differential signal for port B
2	CLKA-	I/O	Clock negative differential signal for port A
4	CLKA+	I/O	Clock positive differential signal for port A
7	CLK-	I/O	Clock negative differential signal for COM port
6	CLK+	I/O	Clock positive differential signal for COM port





### **Absolute Maximum Ratings**

Above which useful life may be impaired. For user guidelines, not tested.

V <sub>CC</sub> , Supply Voltage,	0.5V to 4.5V
V <sub>CNTRL</sub> , DC Input Voltage (OE, SEL) <sup>(1)</sup>	0.5V to V <sub>CC</sub>
V <sub>SW</sub> , DC Switch I/O Voltage <sup>(1,2)</sup>	0.3V to 2.5V
I <sub>IK</sub> , DC Input Diodes Current	50mA
I <sub>OUT</sub> , DC Output Current	25mA
T <sub>STG</sub> , Storage Temperature	-65°C to +150°C
Tj, Junction Temperature	125°C
ESD:	
Human Body Model, JEDEC: JESD22-A114, All Pins.	2.0kV
Charged Device Model, JEDEC: JESD22-C101	1.0kV

#### Note:

Stresses greater than those listed under MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### Note:

- 1. The input and output negative ratings may be exceeded if the input and output diode current ratings are observed.
- 2. V<sub>SW</sub> refers to analog data switch paths.

### **Recommended Operating Conditions**

The Recommended operating Conditions table defines the conditions for actual device operation. Recommended operating conditions are specified to ensure optimal performance to the datasheet specifications.

Symbol	Description	<b>Test Conditions</b>	Min.	Max.	Units
V <sub>CC</sub>	Supply Voltage		1.5	3.6	V
V <sub>CNTRL</sub>	Control Input Voltage (SEL, $\overline{\text{OE}}$ ) <sup>(1)</sup>		0	V <sub>CC</sub>	V
77	V C to I MO W Is (CIVE D. CIVIL CIVIL D. DD.)		0	0.5	V
V <sub>SW</sub> Switch I/O Voltage (CLK-, D-, CLKA-	Switch I/O Voltage (CLK-, D-, CLKA-, CLKB-, DA-, DB-)	LP Mode	0	1.3	V
T <sub>A</sub>	Operating Temperature		-40	+85	°C

#### Note:

#### **DC** and Transient Characteristics

All typical values are at  $T_A = 25^{\circ}$ C unless otherwise specified

0 1 1	D ' 4'	T C. 1111	<b>T</b> 7 ( <b>T</b> 7)	$T_A = -40^{\circ} \text{C to} + 85^{\circ} \text{C}$			TT *4 -
Symbol	Description	Test Conditions	$V_{CC}(V)$	Min.	Тур.	Max.	Units
V <sub>IK</sub>	Clamp Diode Voltage (OE, SEL)	$I_{IN} = -18mA$	1.5	-1.2		-0.6	V
$V_{\mathrm{IH}}$	Input Voltage High	SEL, OE	1.5 to 3.3	1.0			V
V <sub>IL</sub>	Input Voltage Low	SEL, OE	1.5 to 3.3			0.5	V
I <sub>IN</sub>	Control Input Leakage (OE, SEL)	V <sub>CNTRL</sub> = 0 to V <sub>CC</sub>	3.3	-1.0		1.0	μΑ
I <sub>NO(OFF)</sub> I <sub>NC(OFF)</sub>	Off Leakage Current of Port CLKA-, DA-, CLKB- and DB-	$V_{SW} = 0.0 \le DATA \le 1.3V$	3.3	-1.0		1.0	μΑ
I <sub>A(ON)</sub>	On Leakage Current of Common Ports (CLK-, D-)	$V_{SW} = 0.0 \le DATA \le 1.3V$	3.3	-1.0		1.0	μΑ
I <sub>OFF</sub>	Power-Off Leakage Current (All I/O Ports)	$V_{SW} = 0.0 \text{ or } 1.3V$	0	-5		5.0	μΑ

<sup>1.</sup> The control inputs must be held HIGH or LOW; they must not float.





	December 1		()	$T_A = -4$			
Symbol	Description Test Conditions		$V_{CC}(V)$	Min.	Тур.	Max.	Units
$I_{OZ}$	Off-State Leakage	$\frac{V_{SW} = 0.0 \le DATA \le 1.3V,}{OE = High}$	3.6	-5		5.0	μΑ
		$I_{ON} = -8 \text{mA}, \overline{OE} = 0 \text{V},$	1.5				
R <sub>ON_MIPI_HS</sub>	Switch On Resistance for HS MIPI	SEL = V <sub>CC</sub> or 0V, CLKA,	2.5		5		Ω
		CLKB, DB- or DA- = $0.2V$	3.3				
$I_{ON} = -$	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5					
R <sub>ON_MIPI_LP</sub>	Switch On Resistance for LP MIPI	SEL = V <sub>CC</sub> or 0V, CLKA,	2.5		5		Ω
		CLKB, DB- or DA- = 1.2V	3.3				
	On Resistance Matching Between	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5				
ΔR <sub>ON_MIPI_HS</sub>	HS MIPI Channels <sup>(1)</sup>	SEL = V <sub>CC</sub> or 0V, CLKA,	2.5		0.2		Ω
	CLKB, DB- or DA- =	CLKB, DB- or DA- = $0.2V$	3.3				
	$\Delta R_{\mathrm{ON\_MIPI\_LP}}$ On Resistance Matching Between LP MIPI Channels $^{(1)}$	$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5		0.2		
$\Delta R_{ON\_MIPI\_LP}$		SEL = V <sub>CC</sub> or 0V, CLKA, CLKB, DB- or DA- = 1.2V	2.5	_			Ω
			3.3				
D		$I_{ON} = -8mA$ , $OE = 0V$ ,	1.5				
R <sub>ON_FLAT_</sub> MIPI_HS	On Resistance Flatness for HS MIPI	SEL = $V_{CC}$ or 0V, CLKA, CLKB, DB- or DA- = 0 to 0.5V	2.5		0.1		Ω
14111 1_110			3.3				
		$I_{ON} = -8mA$ , $\overline{OE} = 0V$ ,	1.5				
R <sub>ON_FLAT_</sub>	On Resistance Flatness for LP MIPI	$SEL = V_{CC}$ or $0V$ , $CLKA$ ,	2.5		0.1		Ω
MIPI_LP		CLKB, DB- or DA- = 0 to 1.3V	3.3				
$I_{CC}$	Quiescent Supply Current	$\frac{V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,}{OE = 0V}$	3.6		11	20	μΑ
I <sub>CCZ</sub>	Quiescent Supply Current (High Impedance)	$\frac{V_{SEL} = 0 \text{ or } V_{CC}, I_{OUT} = 0,}{OE = 0V}$	3.6			1	μΑ
$I_{CCT}$		$V_{SEL} = 0$ or $V_{CC}$ , $\overline{OE} = 1.5V$	3.6		1		μΑ





### **AC Electrical Characteristics**

All typical values are for  $V_{CC} = 3.3V$  and  $T_A = 25^{\circ}C$  unless otherwise specified.

C11	Description	That Can Pittern	V <sub>CC</sub> (V)	$T_A = -40^{\circ} \text{C to } +85^{\circ} \text{C}$			TT 14
Symbol	Description	Test Conditions		Min.	Тур.	Max.	Units
t <sub>INIT</sub>	Initialization Time V <sub>CC</sub> to Output <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		60		μs
$t_{\rm EN}$	Enable Time OE to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		60	150	μs
$t_{ m DIS}$	Disable Time OE to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		35	250	ns
t <sub>ON</sub>	Turn-On Time SEL to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		350	1100	ns
t <sub>OFF</sub>	Turn-Off Time SEL to Output	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.6V	1.5 to 3.6		125	800	ns
$t_{ m BBM}$	Break-Before-Make Time	$ \begin{vmatrix} R_L = 50\Omega, C_L = 0 pF, V_{SW} \\ = 0.6V \end{vmatrix} $	1.5 to 3.6			450	ns
$t_{\mathrm{PD}}$	Propagation Delay <sup>(1)</sup>	$C_L = 0$ pF, $R_L = 50\Omega$	1.5 to 3.6			0.25	ns
O <sub>IRR</sub>	Off Isolation for MIPI <sup>(1)</sup>	$\frac{R_L}{OE} = 50\Omega, f = 1250MHz,$ $\frac{R_L}{OE} = HIGH, V_{SW} = 0.5V$	1.5 to 3.6		-28		dB
$X_{TALK}$	Crosstalk for MIPI <sup>(1)</sup>	$R_L = 50\Omega, f = 1250 MHz, \\ SEL = HIGH, V_{SW} = 0.5V$	1.5 to 3.6		-35		dB
I <sub>LOSS</sub>	Insertion Loss <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF,$ $f = 1250MHz, V_{SW} = 0.5V$	1.5 to 3.6		-0.7		dB
BW	-3db Bandwidth <sup>(1)</sup>	$R_L = 50\Omega, C_L = 0pF, V_{SW}$ = 0.5V	1.5 to 3.6	5	6		GHz

#### Note:

<sup>1.</sup> Guaranteed by characterization.





## **High-Speed-Related AC Electrical Characteristics**

Symbol	B	Total Complete	<b>37</b> (37)	$T_A = -4$	TT:::4.		
	Description	Test Conditions	V <sub>CC</sub> (V)	Min.	Тур.	Max.	Units
t <sub>SK(P)</sub>	D-PHY HS Mode Skew of Opposite Transitions of the Same Output <sup>(1)</sup>	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW} = 0.3V$	1.5 to 3.6		4	8	
	C-PHY HS Mode Skew of 3 channels in same lane	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW} = 0.5V$	1.5 to 3.6		4		ps
	D-PHY HS Mode Skew of all group A or group B channels <sup>(1)</sup>	$R_{L} = 50\Omega, C_{L} = 0pF, V_{SW} = 0.3V$	1.5 to 3.6		6	10	

Note:

## **Capacitance**

Ch -1	Description	That Can liting	$T_A = -\epsilon$			
Symbol Description		<b>Test Conditions</b>	Min.	Тур.	Max.	Units
C <sub>IN</sub>	Control Pin Input Capacitance(1)	$V_{CC} = 0V, f = 1MHz$		2.1		pF
C <sub>ON</sub>	On Capacitance <sup>(1)</sup>	$V_{CC} = 3.3V$ , $\overline{OE} = 0V$ , $f = 1250MHz$ (In HS common value)		1.3		pF
C <sub>OFF</sub>	Off Capacitance <sup>(1)</sup>	$V_{CC}$ or $\overline{OE}$ = 3.3V, f = 1250MHz (Both sides in HS common value)		0.8		pF

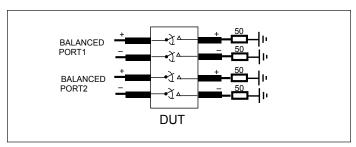
Note:

<sup>1.</sup> Guaranteed by characterization.

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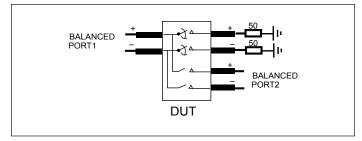


Figure 1. Crosstalk Setup

Figure 2. Off-Isolation Setup

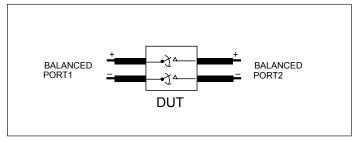


Figure 3. Differential Insertion Loss

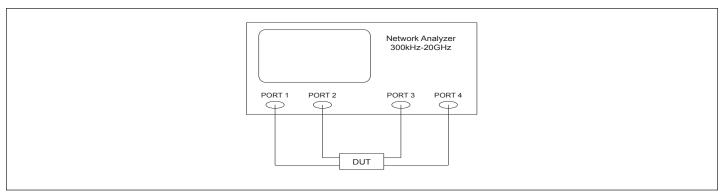
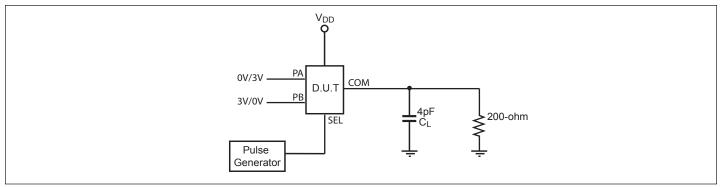


Figure 4. Test Circuit for Dynamic Electrical Characteristics

#### **Test Circuit for Electrical Characteristics**



#### Notes:

- 1.  $C_L$  = Load capacitance: includes jig and probe capacitance.
- 2.  $R_T$  = Termination resistance: should be equal to  $Z_{OUT}$  of the Pulse Generator
- 3. All input impulses are supplied by generators having the following characteristics:  $PRR \leq MHz, Z_O = 50\Omega, t_R \leq 2.5ns, t_F \leq 2.5ns$
- $4.\,$  The outputs are measured one at a time with one transition per measurement.





## **Switching Waveforms**

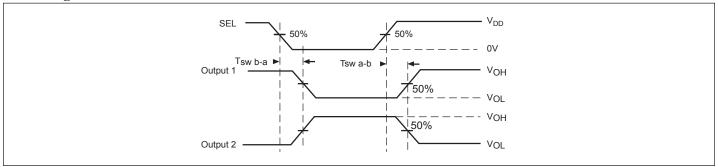


Figure 5. Voltage Waveforms for Select Timing

### **Test Condition**

Output 1 Test Condition	Output 2 Test Condition
PA = Low	PA = High
PB = High	PB = Low

## **Part Marking**



Y: Shortened Date Code (Year) W: Shortened Date Code (Workweek)

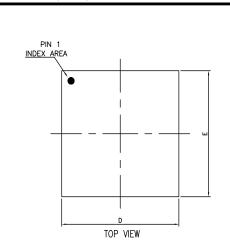
1st X: Assembly Code 2nd X: Fab Code



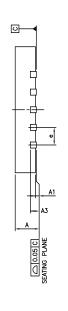


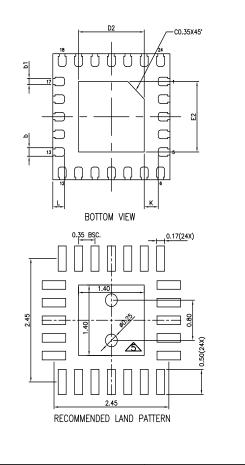
## **Packaging Mechanical**

#### 24-X1QFN (XEB)



SYMBOLS	MIN.	NOM.	MAX.	
Α	0.40	0.45	0.50	
A1	0.00	0.02	0.05	
А3	0.127 REF.			
b	0.12	0.17	0.22	
b1	0.07	0.12	0.17	
D	2.45	2.50	2.55	
Е	2.45	2.50	2.55	
е	0	.35 BS	SC .	
L	0.20	0.25	0.30	
K	0.20	_	_	
D2	1.35	1.40	1.45	
E2	1.35	1.40	1.45	





#### NOTE :

- 1. ALL DIMENSIONS ARE IN mm. ANGLES IN DEGREES.
- 2. COPLANARITY APPLIES TO THE EXPOSED THERMAL PAD AS WELL AS THE TERMINALS.
- 3. REFER JEDEC MO-288
- 4. RECOMMENDED LAND PATTERN IS FOR REFERENCE ONLY.
- 5. THERMAL PAD SOLDERING AREA

DATE: 06/26/19

PERICOM \*\*\*PRODECT CONTROL CON

20-0457

#### For latest package info.

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## Ordering Information

Ordering Code	Package Code	Package Description
PI3WVR626XEBEX	XEB	24-Contact, Extra Thin Fine Pitch (X1QFN) QFN

#### Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. E = Pb-free and Green
- 5. X suffix = Tape/Reel





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